

ABSTRACT:

A method of manufacturing a magnetic tunnel junction device, in which a stack (1) comprising two magnetic layers (3, 7) and a barrier layer (5) extending in between is formed. One of the magnetic layers is structured by means of etching, in which, during etching, a part of this layer is made thinner by removing material until a rest layer (7r) remains. This rest layer is passivated by chemical conversion. In the relevant method, it is prevented that the magnetic layer which is not to be structured is detrimentally influenced during structuring of the other magnetic layer.

Fig. 1E